

Vishay Siliconix

N-Channel 12-V (D-S) MOSFET

PRODUCT SUMMARY						
V _{DS} (V)	$R_{DS(on)}(\Omega)$	I _D (A) ^a	Q _g (Typ.)			
	0.0027 at V _{GS} = 4.5 V	34				
12	0.0032 at V _{GS} = 2.5 V	31	33 nC			
	0.0040 at $V_{GS} = 1.8 \text{ V}$	28				

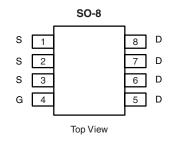
FEATURES

- · Halogen-free
- TrenchFET® Power MOSFET
- 100 % R_q Tested
- 100 % UIS Tested

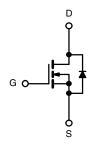


APPLICATIONS

Low V_{IN} DC/DC



 $\textbf{Ordering Information:} \ \text{Si4838BDY-T1-GE3 (Lead (Pb)-free and Halogen-free)}$



N-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS	S T _A = 25 °C, unles	ss otherwise no	oted		
Parameter	Symbol	Limit	Unit		
Drain-Source Voltage	V_{DS}	12	V		
Gate-Source Voltage	V_{GS}	± 8	¬		
	T _C = 25 °C		34		
Continuous Drain Current (T _{.I} = 150 °C)	T _C = 70 °C		27		
Continuous Diairi Current (1) = 150 C)	T _A = 25 °C	I _D	22.5 ^{b, c}		
	T _A = 70 °C		18.0 ^{b, c}		
Pulsed Drain Current	<u>.</u>	I _{DM}	70	A	
Continuous Course Drain Diade Current	T _C = 25 °C	I-	5.1		
Continuous Source-Drain Diode Current	T _A = 25 °C	I _S	2.2 ^{b, c}		
Single Pulse Avalanche Current	L = 0.1 mH	I _{AS}	20		
Avalanche Energy	L = 0.1 mm	E _{AS}	20	mJ	
	T _C = 25 °C		5.7		
Maximum Davies Dissination	T _C = 70 °C	ь	3.6	10/	
Maximum Power Dissipation	T _A = 25 °C	- P _D	2.50 ^{b, c}	w	
	T _A = 70 °C		1.6 ^{b, c}		
Operating Junction and Storage Temperature R	T _J , T _{stg}	- 55 to 150	°C		

THERMAL RESISTANCE RATINGS						
Parameter		Symbol	Typical	Maximum	Unit	
Maximum Junction-to-Ambient ^{b,d}	t ≤ 10 s	R _{thJA}	39	50	°C/W	
Maximum Junction-to-Foot (Drain)	Steady State	R _{thJF}	18	22	J/ VV	

Notes

- a. Based on $T_C = 25$ °C.
- b. Surface Mounted on 1" x 1" FR4 board.
- c. t = 10 s.
- d. Maximum under Steady State conditions is 85 °C/W.

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Si4838BDY

Vishay Siliconix



Parameter Symbol Test Conditions Min. Typ. Max. Unit Static	SPECIFICATIONS $T_J = 25$ °C,	unless othe	erwise noted					
Drain-Source Breakdown Voltage VDB VGB = 0 V, ID = 250 μA 12 VDB	Parameter	Symbol	Test Conditions	Min.	Тур.	Max.	Unit	
V _{DS} Temperature Coefficient ΔV _{OS} (T _J) I _D = 250 μA 12 mV/°C V _{OS(M)} Temperature Coefficient ΔV _{OS(M)} T _J V _{DS} = V _{OS} , I _D = 250 μA 0.4 1.0 V Gate-Source Threshold Voltage I _{OSS} V _{DS} = V _{OS} , I _D = 250 μA 0.4 1.0 V Zero Gate Voltage Drain Current I _{OSS} V _{DS} = 12 V, V _{OS} = 0 V 1 1 μA On-State Drain Current ¹⁴ I _{D(m)} V _{DS} = 12 V, V _{OS} = 0 V, T _D = 55°C 0 10 0 Drain-Source On-State Resistance ¹⁰ P _{OS} = 15 V, V _{OS} = 0 V, T _D = 15 A 0.0021 0.0027 0 Forward Transconductance ¹⁰ 9th V _{DS} = 15 V, I _D = 15 A 0.0021 0.0027 0 Forward Transconductance ¹⁰ 9th V _{DS} = 15 V, I _D = 16 A 105 S S Dynamic ¹ Input Capacitance C _{OSS} V _{DS} = 6 V, V _{GS} = 0 V, f = 1 MHz 1730 0 0 0 pF Reverse Transfer Capacitance C _{OSS} V _{DS} = 6 V, V _{GS} = 2.5 V, I _D = 10 A 56 84 0 <	Static	•				•		
Vos(th) Vos	Drain-Source Breakdown Voltage	V_{DS}	$V_{GS} = 0 \text{ V}, I_D = 250 \mu\text{A}$	12			V	
V _{SS(P)} Temperature Coefficient AV _{SS(P)} V _{SS} (P) V _{DS} = V _{SS} (I _D = 250 μA 0.4 1.0 V Gate-Source Threshold Voltage V _{SS} (P) V _{DS} = 0.V, V _{SS} = 8 V ± 100 nA Zero Gate Voltage Drain Current I _{DSS} V _{DS} = 12.V, V _{SS} = 0.V 1 μ _D On-State Drain Current ^a I _{D(On)} V _{DS} = 2.5 V, V _{DS} = 4.5 V 30 A Drain-Source On-State Resistance ^a R _{DS(On)} V _{DS} = 4.5 V, I _D = 15 A 0.0021 0.0027 Promard Transconductance ^a 9 fs V _{DS} = 15 V, I _D = 10 A 0.0021 0.0027 Forward Transconductance ^a 9 fs V _{DS} = 15 V, I _D = 10 A 0.0021 0.0021 Forward Transconductance ^a 9 fs V _{DS} = 6 V, V _{GS} = 0 V, I = 1 MHz 5760 S Pypamice ^b V _{DS} = 6 V, V _{GS} = 0 V, I = 1 MHz 1730 P _{DF} Input Capacitance C _{ISS} V _{DS} = 6 V, V _{GS} = 2.5 V, I _D = 10 A 5.9 P _D Reverse Transfer Capacitance C _{ISS} V _{DS} = 6 V, V _{GS} = 2.5 V, I _D = 10 A 5.9 1.145 1.5 Gate-Drain Charge	V _{DS} Temperature Coefficient	$\Delta V_{DS}/T_{J}$	L = 250 HA		12		mV/°C	
Seed - Source Leakage	V _{GS(th)} Temperature Coefficient	$\Delta V_{GS(th)}/T_J$	1 _D = 250 μΑ		- 3.2			
Variety Var	Gate-Source Threshold Voltage	V _{GS(th)}	$V_{DS} = V_{GS}, I_{D} = 250 \mu A$	0.4		1.0	V	
Description	Gate-Source Leakage	I _{GSS}	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 8 \text{ V}$			± 100	nA	
On-State Drain Current ^a I _{D(on)} V _{DS} = 12, V, V _{GS} = 4.5 V, V _{GS} = 4.5 V 30 A Drain-Source On-State Resistance ^a R _{DS(on)} V _{DS} = 5.V, V _{GS} = 4.5 V, I _D = 15 A 0.0021 0.0022 Drain-Source On-State Resistance ^a g _{Is} V _{DS} = 18.V, I _D = 10 A 0.0021 0.0025 0.0031 Forward Transconductance ^a g _{Is} V _{DS} = 15.V, I _D = 15 A 105 S Dynamic ^b Input Capacitance C _{Iss} V _{DS} = 6 V, V _{GS} = 0 V, f = 1 MHz 1730 pF Reverse Transfer Capacitance C _{Iss} V _{DS} = 6 V, V _{GS} = 4.5 V, I _D = 10 A 56 84 Reverse Transfer Capacitance C _{Iss} V _{DS} = 6 V, V _{GS} = 2.5 V, I _D = 10 A 56 84 Gate-Source Charge Q _{gs} V _{DS} = 6 V, V _{GS} = 2.5 V, I _D = 10 A 56 84 Gate-Source Charge Q _{gs} V _{DS} = 6 V, V _{GS} = 2.5 V, I _D = 10 A 56 84 Turn-Off Delay Time I _{d(on)} V _{DS} = 6 V, V _{GS} = 2.5 V, I _D = 10 A 2.9 55 Fall Time I _t V _{DD} = 6 V, R _L = 0.6 Ω 2.9 55	Zava Cata Valtaga Dvain Curvant	,	V _{DS} = 12 V, V _{GS} = 0 V			1		
Page	zero Gate voltage Drain Current	'DSS	V _{DS} = 12 V, V _{GS} = 0 V, T _J = 55 °C			10	μΑ	
$ \begin{array}{ c c c c c c c c c c c c c c c c c c c$	On-State Drain Current ^a	I _{D(on)}	$V_{DS} \ge 5 \text{ V}, V_{GS} = 4.5 \text{ V}$	30			Α	
V _{GS} = 1.8 V, I _D = 10 A 0.0031 0.0040			$V_{GS} = 4.5 \text{ V}, I_D = 15 \text{ A}$		0.0021	0.0027	Ω	
Forward Transconductance ^a 9fs V _{DS} = 15 V, I _D = 15 A 105 S Dynamic ^b Input Capacitance C _{ISS} V _{DS} = 6 V, V _{GS} = 0 V, f = 1 MHz 1730 pF Output Capacitance C _{OSS} V _{DS} = 6 V, V _{GS} = 0 V, f = 1 MHz 1730 pF Reverse Transfer Capacitance C _{Crss} 11145 1145 1145 Total Gate Charge Q _g 56 84 84 33 50 70 Gate-Source Charge Q _{gs} 59 1 33 50 70	Drain-Source On-State Resistance ^a	R _{DS(on)}	$V_{GS} = 2.5 \text{ V}, I_D = 12 \text{ A}$		0.0025	0.0032		
Input Capacitance			V _{GS} = 1.8 V, I _D = 10 A		0.0031	0.0040		
$ \begin{array}{ c c c c c c c c c } \hline Input Capacitance & C_{Iss} \\ \hline Output Capacitance & C_{oss} \\ \hline Output Capacitance & C_{oss} \\ \hline Reverse Transfer Capacitance & C_{rss} \\ \hline Total Gate Charge & Q_g \\ \hline Gate-Source Charge & Q_g \\ \hline Gate-Drain Charge & Q_g \\ \hline Gate-Brain Charge & Q_g \\ \hline Gate-Brain Charge & Q_g \\ \hline Gate-Drain Charge & Q_g \\ \hline Gate-Drain Charge & Q_g \\ \hline Gate-Drain Charge & Q_g \\ \hline Gate-Brain Charge & Q_g \\ \hline Gate-Brain Charge & Q_g \\ \hline Gate Resistance & R_g \\ \hline Rise Time & t_t \\ \hline Turn-On Delay Time & t_{d(on)} \\ \hline Fall Time & t_t \\ \hline Turn-Off Delay Time & t_{d(ori)} \\ \hline Fall Time & t_t \\ \hline Turn-Off Delay Time & t_{d(ori)} \\ \hline Fall Time & t_t \\ \hline Turn-Off Delay Time & t_{d(ori)} \\ \hline Fall Time & t_t \\ \hline Turn-Off Delay Time & t_{d(ori)} \\ \hline Fall Time & t_t \\ \hline Turn-Off Delay Time & t_{d(ori)} \\ \hline Fall Time & t_t \\ \hline Turn-Off Delay Time & t_{d(ori)} \\ \hline Fall Time & t_t \\ \hline Turn-Off Delay Time & t_{d(ori)} \\ \hline Fall Time & t_t \\ \hline Turn-Off Delay Time & t_{d(ori)} \\ \hline Fall Time & t_t \\ \hline Turn-Off Delay Time & t_{d(ori)} \\ \hline Fall Time & t_t \\ \hline Drain-Source Body Diode Characteristics \\ \hline Drain-Source Body Diode Characteristics \\ \hline Pulse Diode Forward Current & I_S \\ \hline Body Diode Reverse Recovery Time & t_{rr} \\ \hline Body Diode Reverse Recovery Time & t_{rr} \\ \hline Body Diode Reverse Recovery Charge & Q_{rr} \\ \hline Reverse Recovery Fall Time & t_a \\ \hline \end{tabular} \begin{tabular}{c c c c c c c c c c c c c c c c c c c $	Forward Transconductance ^a	9 _{fs}	V _{DS} = 15 V, I _D = 15 A		105		S	
$ \begin{array}{ c c c c c c c c c } \hline Input Capacitance & C_{Iss} \\ \hline Output Capacitance & C_{oss} \\ \hline Output Capacitance & C_{oss} \\ \hline Reverse Transfer Capacitance & C_{rss} \\ \hline Total Gate Charge & Q_g \\ \hline Gate-Source Charge & Q_g \\ \hline Gate-Drain Charge & Q_g \\ \hline Gate-Brain Charge & Q_g \\ \hline Gate-Brain Charge & Q_g \\ \hline Gate-Drain Charge & Q_g \\ \hline Gate-Drain Charge & Q_g \\ \hline Gate-Drain Charge & Q_g \\ \hline Gate-Brain Charge & Q_g \\ \hline Gate-Brain Charge & Q_g \\ \hline Gate Resistance & R_g \\ \hline Rise Time & t_t \\ \hline Turn-On Delay Time & t_{d(on)} \\ \hline Fall Time & t_t \\ \hline Turn-Off Delay Time & t_{d(ori)} \\ \hline Fall Time & t_t \\ \hline Turn-Off Delay Time & t_{d(ori)} \\ \hline Fall Time & t_t \\ \hline Turn-Off Delay Time & t_{d(ori)} \\ \hline Fall Time & t_t \\ \hline Turn-Off Delay Time & t_{d(ori)} \\ \hline Fall Time & t_t \\ \hline Turn-Off Delay Time & t_{d(ori)} \\ \hline Fall Time & t_t \\ \hline Turn-Off Delay Time & t_{d(ori)} \\ \hline Fall Time & t_t \\ \hline Turn-Off Delay Time & t_{d(ori)} \\ \hline Fall Time & t_t \\ \hline Turn-Off Delay Time & t_{d(ori)} \\ \hline Fall Time & t_t \\ \hline Turn-Off Delay Time & t_{d(ori)} \\ \hline Fall Time & t_t \\ \hline Drain-Source Body Diode Characteristics \\ \hline Drain-Source Body Diode Characteristics \\ \hline Pulse Diode Forward Current & I_S \\ \hline Body Diode Reverse Recovery Time & t_{rr} \\ \hline Body Diode Reverse Recovery Time & t_{rr} \\ \hline Body Diode Reverse Recovery Charge & Q_{rr} \\ \hline Reverse Recovery Fall Time & t_a \\ \hline \end{tabular} \begin{tabular}{c c c c c c c c c c c c c c c c c c c $	Dynamic ^b					l		
$ \begin{array}{c ccccccccccccccccccccccccccccccccccc$	•	C _{iss}			5760			
$ \begin{array}{c ccccccccccccccccccccccccccccccccccc$			V _{DS} = 6 V, V _{GS} = 0 V, f = 1 MHz		1730		pF	
$ \begin{array}{c ccccccccccccccccccccccccccccccccccc$	Reverse Transfer Capacitance				1145			
$ \begin{array}{c ccccccccccccccccccccccccccccccccccc$	·		V _{DS} = 6 V, V _{GS} = 4.5 V, I _D = 10 A			84	nC	
$ \begin{array}{c ccccccccccccccccccccccccccccccccccc$	Total Gate Charge	Q_g			33	50		
$ \begin{array}{c ccccccccccccccccccccccccccccccccccc$	Gate-Source Charge	Q _{qs}	V _{DS} = 6 V, V _{GS} = 2.5 V, I _D = 10 A		5.9			
$ \begin{array}{c ccccccccccccccccccccccccccccccccccc$	Gate-Drain Charge	_			12.5			
$ \begin{array}{c ccccccccccccccccccccccccccccccccccc$	Gate Resistance	R _q	f = 1 MHz	0.2	0.65	1.3	Ω	
Rise Time t_r $V_{DD} = 6 \text{ V}, R_L = 0.6 \Omega$ 29 55 Turn-Off Delay Time $t_{d(off)}$ 10 ± 10 Å, $V_{GEN} = 4.5 \text{ V}, R_g = 1 \Omega$ 140 240 Fall Time t_f 35 65 Turn-On Delay Time t_r $V_{DD} = 6 \text{ V}, R_L = 0.6 \Omega$ 12 24 Rise Time t_r $V_{DD} = 6 \text{ V}, R_L = 0.6 \Omega$ 13 26 Turn-Off Delay Time $t_d(off)$ $t_{DE} = 10 \text{ A}, V_{GEN} = 8 \text{ V}, R_g = 1 \Omega$ 56 100 Fall Time t_f $t_{DE} = 10 \text{ A}, V_{GEN} = 8 \text{ V}, R_g = 1 \Omega$ 56 100 Drain-Source Body Diode Characteristics $t_{DE} = 10 \text{ A}, V_{GEN} = 8 \text{ V}, R_g = 1 \Omega$ 56 100 Continuous Source-Drain Diode Current t_g t_g t_g t_g t_g Pulse Diode Forward Current ^a t_g t_g t_g t_g t_g Body Diode Voltage t_g	Turn-On Delay Time				25	50		
$ \begin{array}{c ccccccccccccccccccccccccccccccccccc$	Rise Time		$V_{DD} = 6 \text{ V}, R_{L} = 0.6 \Omega$		29	55	-	
$ \begin{array}{c ccccccccccccccccccccccccccccccccccc$	Turn-Off Delay Time	t _{d(off)}	$I_D \cong 10 \text{ A}, V_{GEN} = 4.5 \text{ V}, R_g = 1 \Omega$		140	240		
$\begin{array}{c ccccccccccccccccccccccccccccccccccc$	Fall Time	1			35	65		
$\begin{array}{c ccccccccccccccccccccccccccccccccccc$	Turn-On Delay Time	t _{d(on)}			12	24	ns	
Fall Time t_f 10 20 Drain-Source Body Diode Characteristics Continuous Source-Drain Diode Current t_S $t_C = 25 ^{\circ}\text{C}$ 5.1 A Pulse Diode Forward Current t_S $t_S = 3 ^{\circ}\text{A}$ 0.60 1.1 V Body Diode Reverse Recovery Time t_{rr} Body Diode Reverse Recovery Charge t_S $t_S = 10 ^{\circ}\text{A}$ $t_S = 10 ^{\circ}$	Rise Time		$V_{DD} = 6 \text{ V}, R_{L} = 0.6 \Omega$		13	26		
$ \begin{array}{c ccccccccccccccccccccccccccccccccccc$	Turn-Off Delay Time	t _{d(off)}	$I_D \cong 10 \text{ A}, V_{GEN} = 8 \text{ V}, R_g = 1 \Omega$		56	100		
	Fall Time	1			10	20		
Pulse Diode Forward Current ^a I_{SM} T_{O} T_{O	Drain-Source Body Diode Characteristics							
Pulse Diode Forward Current ^a I_{SM} 70 Body Diode Voltage V_{SD} $I_S = 3$ A 0.60 1.1 V Body Diode Reverse Recovery Time t_{rr} 52 100 ns Body Diode Reverse Recovery Charge Q_{rr} Reverse Recovery Fall Time t_a $I_F = 10$ A, $dI/dt = 100$ A/ μ s, $T_J = 25$ °C $I_F = 10$ A, I_F	Continuous Source-Drain Diode Current	I _S	T _C = 25 °C			5.1		
Body Diode Reverse Recovery Time t_{rr} Body Diode Reverse Recovery Charge Q_{rr} Reverse Recovery Fall Time t_a $I_F = 10 \text{ A, dl/dt} = 100 \text{ A/}\mu\text{s, T}_J = 25 \text{ °C}$ 21	Pulse Diode Forward Current ^a	I _{SM}				70	A	
Body Diode Reverse Recovery Time t_{rr} 52100nsBody Diode Reverse Recovery Charge Q_{rr} $I_F = 10 \text{ A}$, $dI/dt = 100 \text{ A/μs}$, $T_J = 25 ^{\circ}\text{C}$ 4080nCReverse Recovery Fall Time t_a 21ns	Body Diode Voltage	V_{SD}	I _S = 3 A		0.60	1.1	V	
Body Diode Reverse Recovery Charge Q_{rr} Reverse Recovery Fall Time t_a $I_F = 10 \text{ A, dl/dt} = 100 \text{ A/µs, T}_J = 25 \text{ °C}$ 21	Body Diode Reverse Recovery Time				52	100	ns	
Reverse Recovery Fall Time t _a I _F = 10 A, dl/dt = 100 A/μs, I _J = 25 °C 21	Body Diode Reverse Recovery Charge	ecovery Charge Q			40	80	nC	
ns	Reverse Recovery Fall Time		$I_{\rm F} = 10$ A, al/at = 100 A/ μ s, $I_{\rm J} = 25$ °C		21		ns	
	<u> </u>	t _b			31			

Notes:

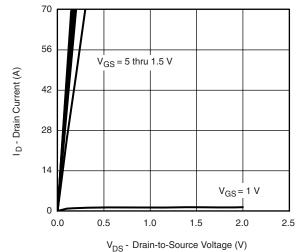
- a. Pulse test; pulse width $\leq 300~\mu s,$ duty cycle $\leq 2~\%.$
- b. Guaranteed by design, not subject to production testing.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

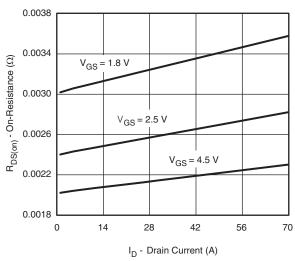


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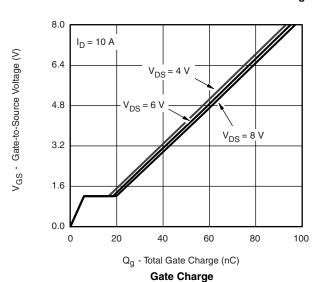
TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted

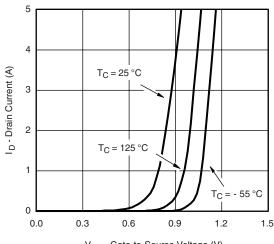


Output Characteristics



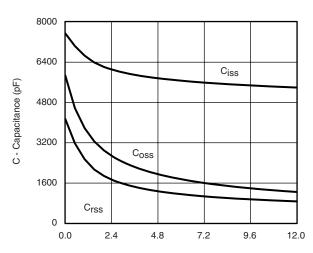
On-Resistance vs. Drain Current and Gate Voltage





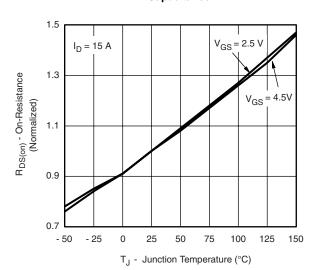
V_{GS} - Gate-to-Source Voltage (V)

Transfer Characteristics



V_{DS} - Drain-to-Source Voltage (V)

Capacitance

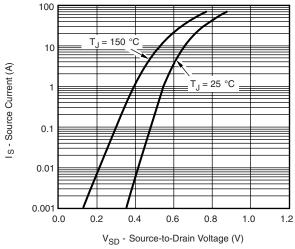


On-Resistance vs. Junction Temperature

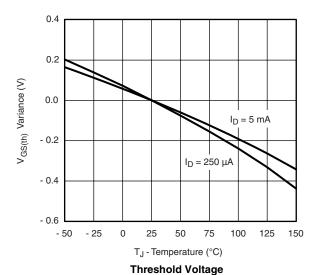
Si4838BDY

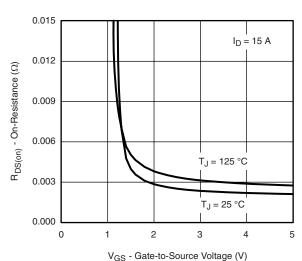
Vishay Siliconix

TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted

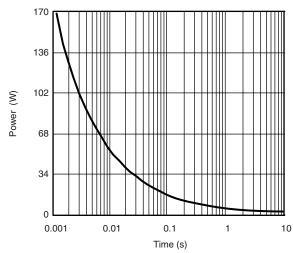


Source-Drain Diode Forward Voltage

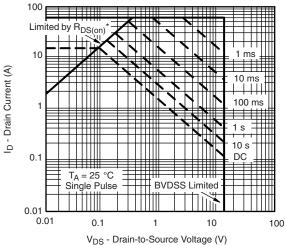




On-Resistance vs. Gate-to-Source Voltage



Single Pulse Power, Junction-to-Ambient

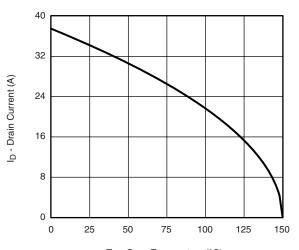


* V_{GS} > minimum V_{GS} at whicht $R_{DS(on)}$ is specified

Safe Operating Area, Junction-to-Ambient

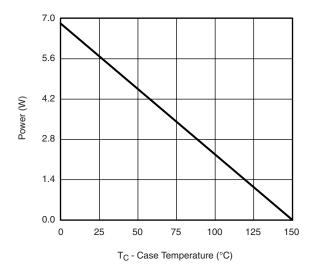
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TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted

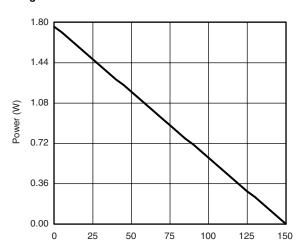


 $T_{\mbox{\scriptsize C}}$ - Case Temperature (°C)

Current Derating*



Power, Junction-to-Foot



T_A - Ambient Temperature (°C)

Power, Junction-to-Ambient

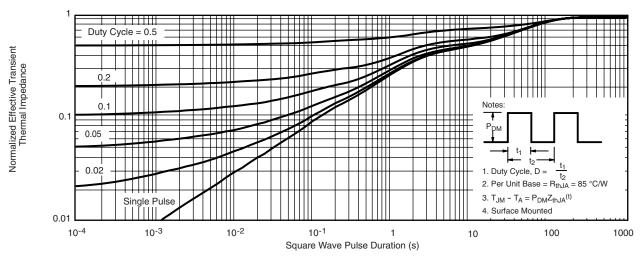
^{*}The power dissipation P_D is based on $T_{J(max)}$ = 150 °C, using junction-to-case thermal resistance, and is more useful in settling the upper dissipation limit for cases where additional heatsinking is used. It is used to determine the current rating, when this rating falls below the package limit.

Si4838BDY

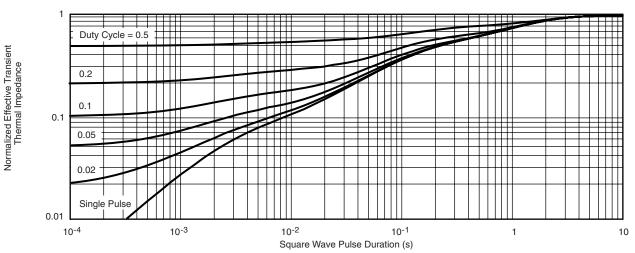
Vishay Siliconix



TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



Normalized Thermal Transient Impedance, Junction-to-Ambient



Normalized Thermal Transient Impedance, Junction-to-Foot

Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package/tape drawings, part marking, and reliability data, see http://www.vishay.com/ppg?68964.



SOIC (NARROW): 8-LEAD JEDEC Part Number: MS-012







	MILLIM	IETERS	INC	INCHES		
DIM	Min	Max	Min	Max		
Α	1.35	1.75	0.053	0.069		
A ₁	0.10	0.20	0.004	0.008		
В	0.35	0.51	0.014	0.020		
С	0.19	0.25	0.0075	0.010		
D	4.80	5.00	0.189	0.196		
E	3.80	4.00	0.150	0.157		
е	1.27	BSC	0.050	BSC		
Н	5.80	6.20	0.228	0.244		
h	0.25	0.50	0.010	0.020		
L	0.50	0.93	0.020	0.037		
q	0°	8°	0°	8°		
S	0.44	0.64	0.018	0.026		
FCN: C-06527-Bey 11-Sen-06						

ECN: C-06527-Rev. I, 11-Sep-06

DWG: 5498

Document Number: 71192 www.vishay.com 11-Sep-06 www.vishay.com



RECOMMENDED MINIMUM PADS FOR SO-8



Recommended Minimum Pads Dimensions in Inches/(mm)

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